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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, I²C, LINbus, SCI, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	149
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	80K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 29x10b, 5x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	176-LQFP
Supplier Device Package	176-LQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5606bk0vlu4

1.3 Device comparison

Table 1 summarizes the functions of the blocks present on the MPC5606BK.

Table 1. MPC5606BK family comparison[1]

Feature	MPC5605BK			MPC5606BK		
Package	100 LQFP	144 LQFP	176 LQFP	100 LQFP	144 LQFP	176 LQFP
CPU	e200z0h					
Execution speed[2]	Up to 64 MHz					
Code flash memory	768 KB			1 MB		
Data flash memory	64 (4 x 16) KB					
SRAM	64 KB			80 KB		
MPU	8-entry					
eDMA	16 ch					
10-bit ADC	Yes					
dedicated[3]	7 ch	15 ch	29 ch	7 ch	15 ch	29 ch
shared with 12-bit ADC	19 ch					
12-bit ADC	Yes					
dedicated[4]	5 ch					
shared with 10-bit ADC	19 ch					
Total timer I/O[5] eMIOS	37 ch, 16-bit	64 ch, 16-bit		37 ch, 16-bit	64 ch, 16-bit	
Counter / OPWM / ICOC[6]	10 ch					
O(I)PWM / OPWFMB / OPWMCB / ICOC[7]	7 ch					
O(I)PWM / ICOC[8]	7 ch	14 ch				
OPWM / ICOC[9]	13 ch	33 ch				
SCI (LINFlex)	4	6	8	4	6	8
SPI (DSPI)	3	5	6	3	5	6
CAN (FlexCAN)	6					
I^2C	1					
32 KHz oscillator	Yes					
GPIO[10]	77	121	149	77	121	149
Debug	JTAG					

1 Feature set dependent on selected peripheral multiplexing; table shows example.

2 Based on 125 °C ambient operating temperature.

3 Not shared with 12-bit ADC, but possibly shared with other alternate functions.

4 Not shared with 10-bit ADC, but possibly shared with other alternate functions.

5 Refer to eMIOS section of device reference manual for information on the channel configuration and functions.

6 Each channel supports a range of modes including Modulus counters, PWM generation, Input Capture, Output Compare.

7 Each channel supports a range of modes including PWM generation with dead time, Input Capture, Output Compare.

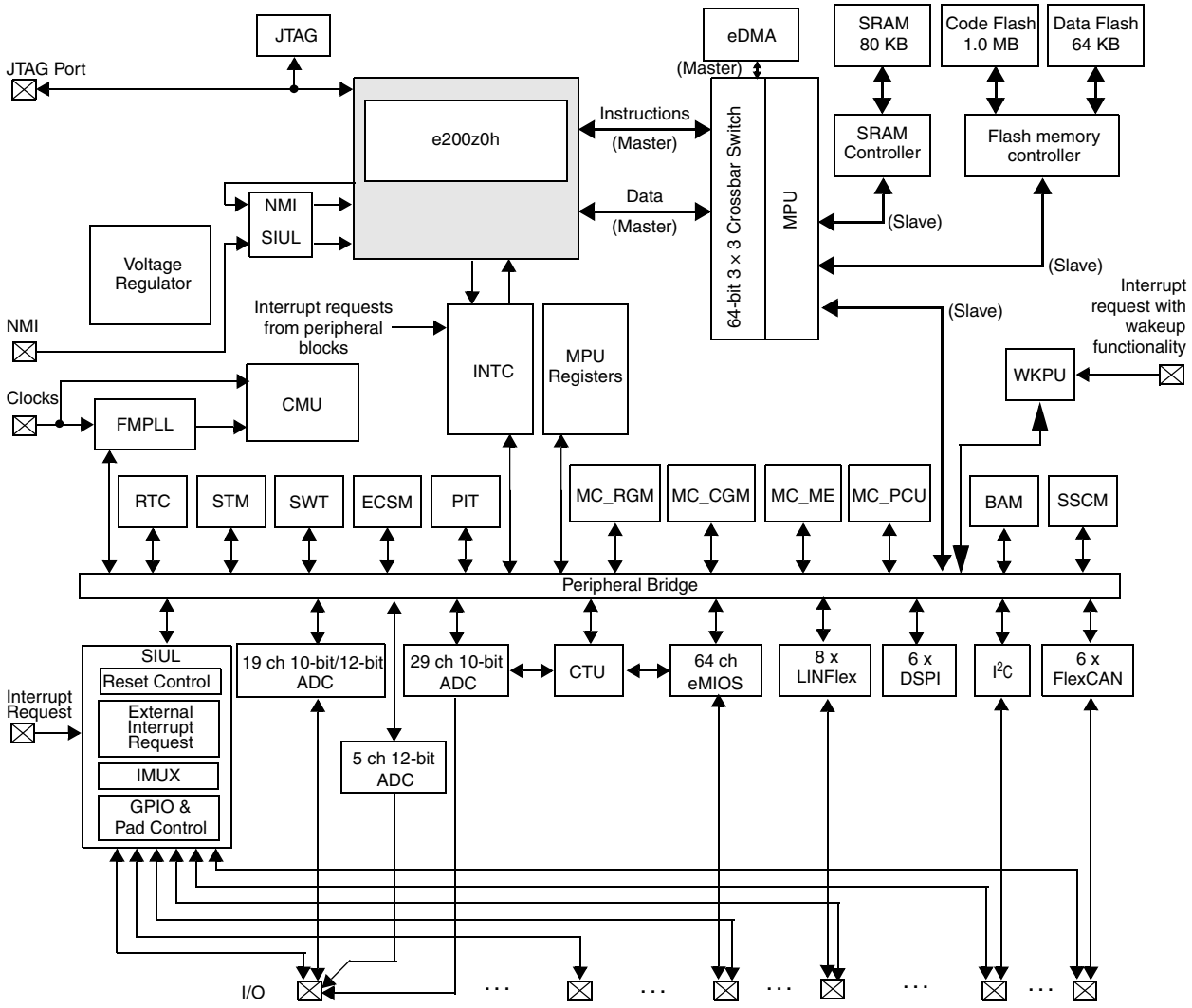
8 Each channel supports a range of modes including PWM generation, Input Capture, Output Compare, Period and Pulse width measurement.

9 Each channel supports a range of modes including PWM generation, Input Capture, and Output Compare.

10 Maximum I/O count based on multiplexing with peripherals.

1.4 Block diagram

Figure 1 shows a top-level block diagram of the MPC5606BK.



Legend:

ADC	Analog-to-Digital Converter
BAM	Boot Assist Module
FlexCAN	Controller Area Network
CFlash	Code flash memory
CMU	Clock Monitor Unit
CTU	Cross Triggering Unit
DFlash	Data flash memory
DSPI	Deserial Serial Peripheral Interface
eDMA	Enhanced Direct Memory Access
eMIOS	Enhanced Modular Input Output System
FMPLL	Frequency-Modulated Phase-Locked Loop
I^2C	Inter-integrated Circuit Bus
IMUX	Internal Multiplexer
INTC	Interrupt Controller
JTAG	JTAG controller
LINFlex	Serial Communication Interface (LIN support)
MC_CGM	Clock Generation Module
MC_ME	Mode Entry Module
MPU	Memory Protection Unit
NMI	Non-Maskable Interrupt
MC_PCU	Power Control Unit
MC_RGM	Reset Generation Module
PIT	Periodic Interrupt Timer
RTC	Real-Time Clock
SIUL	System Integration Unit Lite
SRAM	Static Random-Access Memory
SSCM	System Status Configuration Module
STM	System Timer Module
SWT	Software Watchdog Timer
WKPU	Wakeup Unit

Figure 1. MPC5606BK block diagram

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function[1]	Function	Peripheral	I/O direction	Pad type[2]	RESET config.[3]	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PC[5]	PCR[37]	AF0 AF1 AF2 AF3 —	GPIO[37] SOUT_1 CAN3TX DEBUG[3] EIRQ[7]	SIUL DSPI_1 FlexCAN_3 SSCM SIUL	I/O O O O I	M	Tristate	91	130	158
PC[6]	PCR[38]	AF0 AF1 AF2 AF3	GPIO[38] LIN1TX E1UC[28] DEBUG[4]	SIUL LINFlex_1 eMIOS_1 SSCM	I/O O I/O O	S	Tristate	25	36	44
PC[7]	PCR[39]	AF0 AF1 AF2 AF3 — —	GPIO[39] — E1UC[29] DEBUG[5] LIN1RX WKUP[12][4]	SIUL — eMIOS_1 SSCM LINFlex_1 WKUP	I/O — I/O O I I	S	Tristate	26	37	45
PC[8]	PCR[40]	AF0 AF1 AF2 AF3	GPIO[40] LIN2TX E0UC[3] DEBUG[6]	SIUL LINFlex_2 eMIOS_0 SSCM	I/O O I/O O	S	Tristate	99	143	175
PC[9]	PCR[41]	AF0 AF1 AF2 AF3 — —	GPIO[41] — E0UC[7] DEBUG[7] WKUP[13][4] LIN2RX	SIUL — eMIOS_0 SSCM WKUP LINFlex_2	I/O — I/O O I I	S	Tristate	2	2	2
PC[10]	PCR[42]	AF0 AF1 AF2 AF3	GPIO[42] CAN1TX CAN4TX MA[1]	SIUL FlexCAN_1 FlexCAN_4 ADC_0	I/O O O O	M	Tristate	22	28	36
PC[11]	PCR[43]	AF0 AF1 AF2 AF3 — — —	GPIO[43] — — MA[2] WKUP[5][4] CAN1RX CAN4RX	SIUL — — ADC_0 WKUP FlexCAN_1 FlexCAN_4	I/O — — O I I I	S	Tristate	21	27	35
PC[12]	PCR[44]	AF0 AF1 AF2 AF3 — —	GPIO[44] E0UC[12] — — EIRQ[19] SIN_2	SIUL eMIOS_0 — — SIUL DSPI_2	I/O I/O — — I I	M	Tristate	97	141	173
PC[13]	PCR[45]	AF0 AF1 AF2 AF3	GPIO[45] E0UC[13] SOUT_2 —	SIUL eMIOS_0 DSPI_2 —	I/O I/O O —	S	Tristate	98	142	174

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function[1]	Function	Peripheral	I/O direction	Pad type[2]	RESET config.[3]	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PD[5]	PCR[53]	AF0 AF1 AF2 AF3 — —	GPIO[53] — — — ADC0_P[9] ADC1_P[9]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	46	68	82
PD[6]	PCR[54]	AF0 AF1 AF2 AF3 — —	GPIO[54] — — — ADC0_P[10] ADC1_P[10]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	47	69	83
PD[7]	PCR[55]	AF0 AF1 AF2 AF3 — —	GPIO[55] — — — ADC0_P[11] ADC1_P[11]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	48	70	84
PD[8]	PCR[56]	AF0 AF1 AF2 AF3 — —	GPIO[56] — — — ADC0_P[12] ADC1_P[12]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	49	71	87
PD[9]	PCR[57]	AF0 AF1 AF2 AF3 — —	GPIO[57] — — — ADC0_P[13] ADC1_P[13]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	56	78	94
PD[10]	PCR[58]	AF0 AF1 AF2 AF3 — —	GPIO[58] — — — ADC0_P[14] ADC1_P[14]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	57	79	95
PD[11]	PCR[59]	AF0 AF1 AF2 AF3 — —	GPIO[59] — — — ADC0_P[15] ADC1_P[15]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	58	80	96
PD[12]	PCR[60]	AF0 AF1 AF2 AF3 —	GPIO[60] CS5_0 E0UC[24] — ADC0_S[4]	SIUL DSPI_0 eMIOS_0 — ADC_0	I/O O I/O — I	J	Tristate	—	—	100

3.2.3 NVUSRO[WATCHDOG_EN] field description

The watchdog enable/disable configuration after reset is dependent on the WATCHDOG_EN bit value. Table 7 shows how NVUSRO[WATCHDOG_EN] controls the device configuration.

Table 7. WATCHDOG_EN field description[1]

Value[2]	Description
0	Disable after reset
1	Enable after reset

1 See the *MPC5606BK Microcontroller Reference Manual* for more information on the NVUSRO register.

2 The default manufacturing value is '1'. This value can be programmed by the customer in Shadow Flash.

3.3 Absolute maximum ratings

Table 8. Absolute maximum ratings

Symbol		Parameter	Conditions	Value		Unit
				Min	Max	
V_{SS}	SR	Digital ground on VSS_HV pins	—	0	0	V
V_{DD}	SR	Voltage on VDD_HV pins with respect to ground (V_{SS})	—	–0.3	6.0	V
V_{SS_LV}	SR	Voltage on VSS_LV (low voltage digital supply) pins with respect to ground (V_{SS})	—	V_{SS} – 0.1	V_{SS} + 0.1	V
V_{DD_BV}	SR	Voltage on VDD_BV pin (regulator supply) with respect to ground (V_{SS})	—	–0.3	6.0	V
			Relative to V_{DD}	–0.3	V_{DD} + 0.3	
V_{SS_ADC}	SR	Voltage on VSS_HV_ADC0, VSS_HV_ADC1 (ADC reference) pin with respect to ground (V_{SS})	—	V_{SS} – 0.1	V_{SS} + 0.1	V
V_{DD_ADC}	SR	Voltage on VDD_HV_ADC0, VDD_HV_ADC1 (ADC reference) with respect to ground (V_{SS})	—	–0.3	6.0	V
			Relative to V_{DD}	V_{DD} – 0.3	V_{DD} + 0.3	
V_{IN}	SR	Voltage on any GPIO pin with respect to ground (V_{SS})	—	–0.3	6.0	V
			Relative to V_{DD}	—	V_{DD} + 0.3	
I_{INJPAD}	SR	Injected input current on any pin during overload condition	—	–10	10	mA
I_{INJSUM}	SR	Absolute sum of all injected input currents during overload condition	—	–50	50	
I_{AVGSEG}	SR	Sum of all the static I/O current within a supply segment	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	70	mA
			V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	64	
$T_{STORAGE}$	SR	Storage temperature	—	–55	150	°C

Table 10. Recommended operating conditions (5.0 V) (continued)

Symbol		Parameter	Conditions	Value		Unit
				Min	Max	
V_{DD_ADC}[5]	SR	Voltage on VDD_HV_ADC0, VDD_HV_ADC1 (ADC reference) with respect to ground (V_{SS})	—	4.5	5.5	V
			Voltage drop[2]	3.0	5.5	
			Relative to V_{DD}	V_{DD} – 0.1	V_{DD} + 0.1	
V_{IN}	SR	Voltage on any GPIO pin with respect to ground (V_{SS})	—	V_{SS} – 0.1	—	V
			Relative to V_{DD}	—	V_{DD} + 0.1	
I_{INJPAD}	SR	Injected input current on any pin during overload condition	—	–5	5	mA
I_{INJSUM}	SR	Absolute sum of all injected input currents during overload condition	—	–50	50	
TV_{DD}	SR	V_{DD} slope to ensure correct power up[6]	—	3.0[7]	0.25 V/µs	V/s
T_{A} C-Grade Part	SR	Ambient temperature under bias	f_{CPU} < 64 MHz[8]	–40	85	°C
T_{J} C-Grade Part	SR	Junction temperature under bias	—	–40	110	
T_{A} V-Grade Part	SR	Ambient temperature under bias	f_{CPU} < 64 MHz[8]	–40	105	
T_{J} V-Grade Part	SR	Junction temperature under bias	—	–40	130	
T_{A} M-Grade Part	SR	Ambient temperature under bias	f_{CPU} < 64 MHz[8]	–40	125	
T_{J} M-Grade Part	SR	Junction temperature under bias	—	–40	150	

1 100 nF capacitance needs to be provided between each V_{DD}/V_{SS} pair.

2 Full device operation is guaranteed by design when the voltage drops below 4.5 V down to 3.0 V. However, certain analog electrical characteristics will not be guaranteed to stay within the stated limits.

3 330 nF capacitance needs to be provided between each V_{DD_LV}/V_{SS_LV} supply pair.

4 470 nF capacitance needs to be provided between V_{DD_BV} and the nearest V_{SS_LV} (higher value may be needed depending on external regulator characteristics). While the supply voltage ramps up, the slope on V_{DD_BV} should be less than $0.9V_{DD\_HV}$ in order to ensure the device does not enter regulator bypass mode.

5 100 nF capacitance needs to be provided between V_{DD_ADC}/V_{SS_ADC} pair.

6 Guaranteed by device validation. Please refer to Section 3.5.1, External ballast resistor recommendations for minimum V_{DD} slope to be guaranteed to ensure correct power up in case of external resistor usage.

7 Minimum value of TV_{DD} must be guaranteed until V_{DD} reaches 2.6 V (maximum value of V_{PORH}).

8 This frequency includes the 4% frequency modulation guard band.

NOTE

RAM data retention is guaranteed with V_{DD_LV} not below 1.08 V.

Table 15. MEDIUM configuration output buffer electrical characteristics (continued)

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
V_{OL}	CC	C	Output low level MEDIUM configuration	Push Pull	I_{OL} = 3.8 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	$0.2V_{DD}$	V
		P			I_{OL} = 2 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 (recommended)	—	—	$0.1V_{DD}$	
		C			I_{OL} = 1 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 1[2]	—	—	$0.1V_{DD}$	
		C			I_{OL} = 1 mA, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	—	—	0.5	
		C			I_{OL} = 100 µA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	$0.1V_{DD}$	

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

2 The configuration PAD3V5 = 1 when V_{DD} = 5 V is only a transient configuration during power-up. All pads but RESET are configured in input or in high impedance state.

Table 16. FAST configuration output buffer electrical characteristics

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
V_{OH}	CC	P	Output high level FAST configuration	Push Pull	I_{OH} = –14 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 (recommended)	$0.8V_{DD}$	—	—	V
		C			I_{OH} = –7 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 1[2]	$0.8V_{DD}$	—	—	
		C			I_{OH} = –11 mA, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	V_{DD} – 0.8	—	—	
V_{OL}	CC	P	Output low level FAST configuration	Push Pull	I_{OL} = 14 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 (recommended)	—	—	$0.1V_{DD}$	V
		C			I_{OL} = 7 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 1[2]	—	—	$0.1V_{DD}$	
		C			I_{OL} = 11 mA, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	—	—	0.5	

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

Table 20. I/O weight[1] (continued)

Supply segment			Pad	176 LQFP				144/100 LQFP			
				Weight 5 V		Weight 3.3 V		Weight 5 V		Weight 3.3 V	
176 LQFP	144 LQFP	100 LQFP		SRC[2] = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1
1	—	—	PH[15]	2%	3%	3%	3%	—	—	—	—
	—	—	PH[13]	3%	4%	3%	4%	—	—	—	—
	—	—	PH[14]	3%	4%	4%	4%	—	—	—	—
	—	—	PI[6]	4%	—	4%	—	—	—	—	—
	—	—	PI[7]	4%	—	4%	—	—	—	—	—
	4	—	PG[5]	4%	—	5%	—	10%	—	12%	—
		—	PG[4]	4%	6%	5%	5%	9%	13%	11%	12%
		—	PG[3]	4%	—	5%	—	9%	—	11%	—
		—	PG[2]	4%	6%	5%	5%	9%	12%	10%	11%
		4	PA[2]	4%	—	5%	—	8%	—	10%	—
			PE[0]	4%	—	5%	—	8%	—	9%	—
			PA[1]	4%	—	5%	—	8%	—	9%	—
			PE[1]	4%	6%	5%	6%	7%	10%	9%	9%
			PE[8]	4%	6%	5%	6%	7%	10%	8%	9%
			PE[9]	4%	—	5%	—	6%	—	8%	—
			PE[10]	4%	—	5%	—	6%	—	7%	—
			PA[0]	4%	6%	5%	5%	6%	8%	7%	7%
			PE[11]	4%	—	5%	—	5%	—	6%	—

Table 20. I/O weight[1] (continued)

Supply segment			Pad	176 LQFP				144/100 LQFP			
				Weight 5 V		Weight 3.3 V		Weight 5 V		Weight 3.3 V	
176 LQFP	144 LQFP	100 LQFP		SRC[2] = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1
6	4	4	PC[0]	6%	9%	7%	8%	7%	10%	8%	8%
			PH[9]	7%	—	8%	—	7%	—	9%	—
			PE[2]	7%	10%	8%	9%	8%	11%	9%	10%
			PE[3]	7%	10%	9%	9%	8%	12%	10%	10%
			PC[5]	7%	11%	9%	9%	8%	12%	10%	11%
			PC[4]	8%	11%	9%	10%	9%	13%	10%	11%
			PE[4]	8%	11%	9%	10%	9%	13%	11%	12%
			PE[5]	8%	11%	10%	10%	9%	14%	11%	12%
		—	PH[4]	8%	12%	10%	10%	10%	14%	12%	12%
		—	PH[5]	8%	—	10%	—	10%	—	12%	—
		—	PH[6]	8%	12%	10%	11%	10%	15%	12%	13%
		—	PH[7]	9%	12%	10%	11%	11%	15%	13%	13%
		—	PH[8]	9%	12%	10%	11%	11%	16%	13%	14%
		4	PE[6]	9%	12%	10%	11%	11%	16%	13%	14%
			PE[7]	9%	12%	10%	11%	11%	16%	14%	14%
	—	—	PI[3]	9%	—	10%	—	—	—	—	—
	—	—	PI[2]	9%	—	10%	—	—	—	—	—
	—	—	PI[1]	9%	—	10%	—	—	—	—	—
	—	—	PI[0]	9%	—	10%	—	—	—	—	—
	4	4	PC[12]	8%	12%	10%	11%	12%	18%	15%	16%
			PC[13]	8%	—	10%	—	13%	—	15%	—
			PC[8]	8%	—	10%	—	13%	—	15%	—
			PB[2]	8%	11%	9%	10%	13%	18%	15%	16%

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

2 SRC is the Slew Rate Control bit in SIU_PCR*x*

3.7 $\overline{\text{RESET}}$ electrical characteristics

The device implements a dedicated bidirectional $\overline{\text{RESET}}$ pin.

Table 22. Voltage regulator electrical characteristics (continued)

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
$I_{MREGINT}$	CC	D	Main regulator module current consumption	I_{MREG} = 200 mA	—	—	2	mA
				I_{MREG} = 0 mA	—	—	1	
V_{LPREG}	CC	P	Low power regulator output voltage	After trimming	1.15	1.23	1.32	V
I_{LPREG}	SR	—	Low power regulator current provided to V_{DD_LV} domain	—	—	—	15	mA
$I_{LPREGINT}$	CC	D	Low power regulator module current consumption	I_{LPREG} = 15 mA; T_A = 55 °C	—	—	600	µA
		—		I_{LPREG} = 0 mA; T_A = 55 °C	—	5	—	
V_{ULPREG}	CC	P	Ultra low power regulator output voltage	After trimming	1.15	1.23	1.32	V
I_{ULPREG}	SR	—	Ultra low power regulator current provided to V_{DD_LV} domain	—	—	—	5	mA
$I_{ULPREGINT}$	CC	D	Ultra low power regulator module current consumption	I_{ULPREG} = 5 mA; T_A = 55 °C	—	—	100	µA
				I_{ULPREG} = 0 mA; T_A = 55 °C	—	2	—	
I_{DD_BV}	CC	D	Inrush average current on V_{DD_BV} during power-up[5]	—	—	—	300[6]	mA
$\left\|\frac{d}{dt}VDD\right\|$	SR	—	Maximum slope on VDD	—	—	—	250	mV/µs
$\|\Delta_{VDD(STDBY))}\|$	SR	—	Maximum instant variation on VDD during STANDBY exit	—	—	—	30	mV
$\left\|\frac{d}{dt}VDD(STDBY)\right\|$	SR	—	Maximum slope on VDD during STANDBY exit	—	—	—	15	mV/µs

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

2 This capacitance value is driven by the constraints of the external voltage regulator supplying the V_{DD_BV} voltage. A typical value is in the range of 470 nF.

3 This value is acceptable to guarantee operation from 4.5 V to 5.5 V

4 External regulator and capacitance circuitry must be capable of providing I_{DD_BV} while maintaining supply V_{DD_BV} in operating range.

5 Inrush current is seen only for short time during power-up and on standby exit (max 20 µs, depending on external capacitances to be load).

6 The duration of the inrush current depends on the capacitance placed on LV pins. BV decoupling capacitors must be sized accordingly. Refer to I_{MREG} value for minimum amount of current to be provided in cc.

3.8.2 Voltage monitor electrical characteristics

The device implements a Power-on Reset module to ensure correct power-up initialization, as well as four low voltage detectors to monitor the V_{DD} and the V_{DD_LV} voltage while device is supplied:

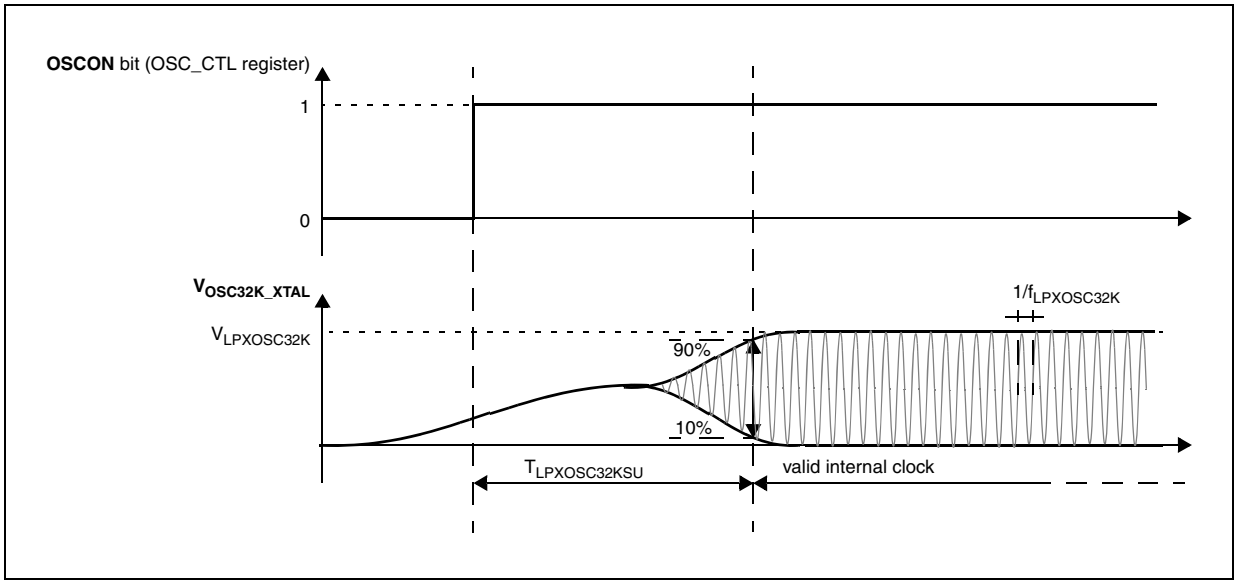


Figure 16. Slow external crystal oscillator (32 kHz) electrical characteristics

Table 36. Slow external crystal oscillator (32 kHz) electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
f_{SXOSC}	SR	—	Slow external crystal oscillator frequency	—	32	32.768	40	kHz
V_{SXOSC}	CC	T	Oscillation amplitude	—	—	2.1	—	V
$I_{SXOSCBIAS}$	CC	T	Oscillation bias current	—		2.5		µA
I_{SXOSC}	CC	T	Slow external crystal oscillator consumption	—	—	—	8	µA
$T_{SXOSCSU}$	CC	T	Slow external crystal oscillator start-up time	—	—	—	2[2]	s

[1] V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

[2] Start-up time has been measured with EPSON TOYOCOM MC306 crystal. Variation may be seen with other crystal.

3.14 FMPLL electrical characteristics

The device provides a frequency modulated phase locked loop (FMPLL) module to generate a fast system clock from the FXOSC or FIRC sources.

Table 37. FMPLL electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
f_{PLLIN}	SR	—	FMPLL reference clock[2]	—	4	—	64	MHz
Δ_{PLLIN}	SR	—	FMPLL reference clock duty cycle[2]	—	40	—	60	%

possible, ideally infinite. This capacitor contributes to attenuating the noise present on the input pin; furthermore, it sources charge during the sampling phase, when the analog signal source is a high-impedance source.

A real filter can typically be obtained by using a series resistance with a capacitor on the input pin (simple RC filter). The RC filtering may be limited according to the value of source impedance of the transducer or circuit supplying the analog signal to be measured. The filter at the input pins must be designed taking into account the dynamic characteristics of the input signal (bandwidth) and the equivalent input impedance of the ADC itself.

In fact a current sink contributor is represented by the charge sharing effects with the sampling capacitance: C_S being substantially a switched capacitance, with a frequency equal to the conversion rate of the ADC, it can be seen as a resistive path to ground. For instance, assuming a conversion rate of 1 MHz, with C_S equal to 3 pF, a resistance of 330 kΩ is obtained ($R_{EQ} = 1 / (fc \times C_S)$, where fc represents the conversion rate at the considered channel). To minimize the error induced by the voltage partitioning between this resistance (sampled voltage on C_S) and the sum of $R_S + R_F + R_L + R_{SW} + R_{AD}$, the external circuit must be designed to respect the Equation 4:

Eqn. 4

$$V_A \bullet \frac{R_S + R_F + R_L + R_{SW} + R_{AD}}{R_{EQ}} < \frac{1}{2} LSB$$

Equation 4 generates a constraint for external network design, in particular on resistive path. Internal switch resistances (R_{SW} and R_{AD}) can be neglected with respect to external resistances.

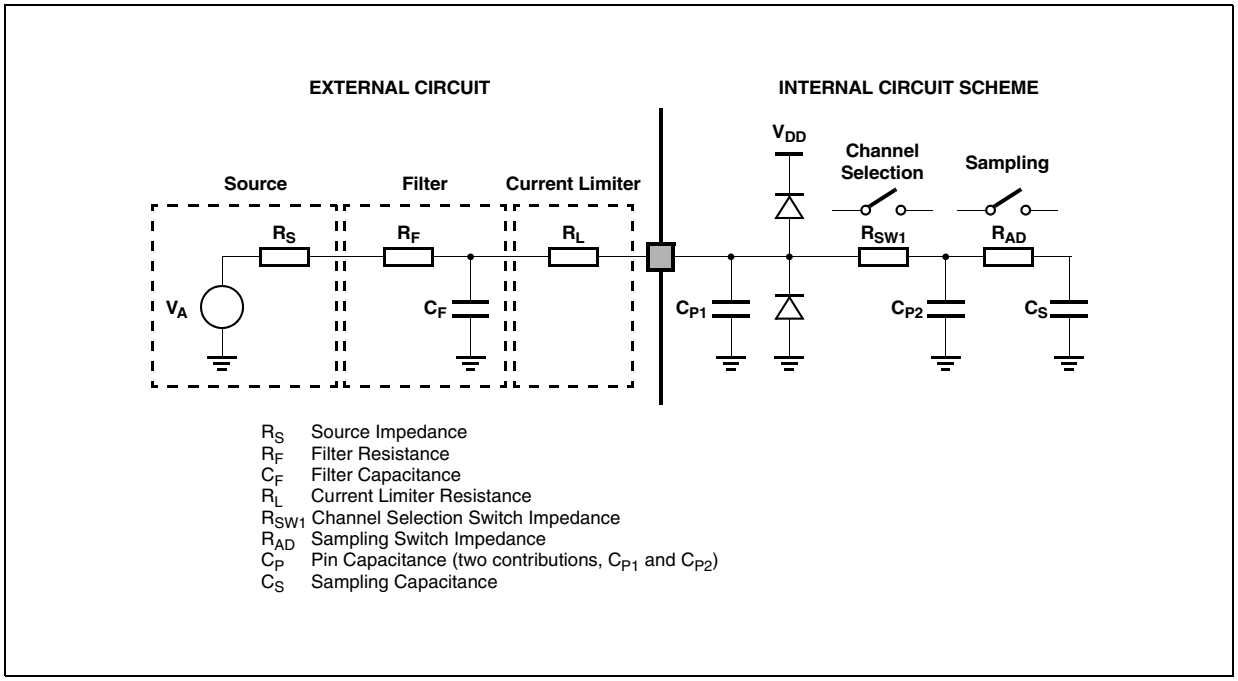


Figure 18. Input equivalent circuit (precise channels)

Eqn. 5

$$\tau_1 = (R_{SW} + R_{AD}) \bullet \frac{C_P \bullet C_S}{C_P + C_S}$$

Equation 5 can again be simplified considering only C_S as an additional worst condition. In reality, the transient is faster, but the A/D converter circuitry has been designed to be robust also in the very worst case: the sampling time T_S is always much longer than the internal time constant:

Eqn. 6

$$\tau_1 < (R_{SW} + R_{AD}) \bullet C_S \ll T_S$$

The charge of C_{P1} and C_{P2} is redistributed also on C_S, determining a new value of the voltage V_{A1} on the capacitance according to Equation 7:

Eqn. 7

$$V_{A1} \bullet (C_S + C_{P1} + C_{P2}) = V_A \bullet (C_{P1} + C_{P2})$$

2. A second charge transfer involves also C_F (that is typically bigger than the on-chip capacitance) through the resistance R_L: again considering the worst case in which C_{P2} and C_S were in parallel to C_{P1} (since the time constant in reality would be faster), the time constant is:

Eqn. 8

$$\tau_2 < R_L \bullet (C_S + C_{P1} + C_{P2})$$

In this case, the time constant depends on the external circuit: in particular imposing that the transient is completed well before the end of sampling time T_S, a constraints on R_L sizing is obtained:

Eqn. 9

$$10 \bullet \tau_2 = 10 \bullet R_L \bullet (C_S + C_{P1} + C_{P2}) < T_S$$

Of course, R_L shall be sized also according to the current limitation constraints, in combination with R_S (source impedance) and R_F (filter resistance). Being C_F definitively bigger than C_{P1}, C_{P2} and C_S, then the final voltage V_{A2} (at the end of the charge transfer transient) will be much higher than V_{A1}. Equation 10 must be respected (charge balance assuming now C_S already charged at V_{A1}):

Eqn. 10

$$V_{A2} \bullet (C_S + C_{P1} + C_{P2} + C_F) = V_A \bullet C_F + V_{A1} \bullet (C_{P1} + C_{P2} + C_S)$$

The two transients above are not influenced by the voltage source that, due to the presence of the $R_F C_F$ filter, is not able to provide the extra charge to compensate the voltage drop on C_S with respect to the ideal source V_A; the time constant $R_F C_F$ of the filter is very high with respect to the sampling time (T_S). The filter is typically designed to act as antialiasing.

Table 41. ADC_0 conversion characteristics (10-bit ADC_0) (continued)

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
R_{SW1}	CC	D	Internal resistance of analog source	—		—	—	3	kΩ
R_{SW2}	CC	D	Internal resistance of analog source	—		—	—	2	kΩ
R_{AD}	CC	D	Internal resistance of analog source	—		—	—	2	kΩ
I_{INJ}	SR	—	Input current Injection	Current injection on one ADC_0 input, different from the converted one	V_{DD} = 3.3 V ± 10%	–5	—	5	mA
					V_{DD} = 5.0 V ± 10%	–5	—	5	
| INL |	CC	T	Absolute value for integral nonlinearity	No overload		—	0.5	1.5	LSB
| DNL |	CC	T	Absolute differential nonlinearity	No overload		—	0.5	1.0	LSB
| OFS |	CC	T	Absolute offset error	—		—	0.5	—	LSB
| GNE |	CC	T	Absolute gain error	—		—	0.6	—	LSB
TUEP	CC	P	Total unadjusted error[7] for precise channels, input only pins	Without current injection		–2	0.6	2	LSB
		T		With current injection		–3	—	3	
TUEX	CC	T	Total unadjusted error[7] for extended channel	Without current injection		–3	1	3	LSB
		T		With current injection		–4		4	

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.

2 Analog and digital V_{SS} **must** be common (to be tied together externally).

3 V_{AINx} may exceed V_{SS_ADC0} and V_{DD_ADC0} limits, remaining on absolute maximum ratings, but the results of the conversion will be clamped respectively to 0x000 or 0x3FF.

4 Duty cycle is ensured by using system clock without prescaling. When ADCLKSEL = 0, the duty cycle is ensured by internal divider by 2.

5 During the sample time the input capacitance C_S can be charged/discharged by the external source. The internal resistance of the analog source must allow the capacitance to reach its final voltage level within t_{ADC0_S}. After the end of the sample time t_{ADC0_S}, changes of the analog input voltage have no effect on the conversion result. Values for the sample clock t_{ADC0_S} depend on programming.

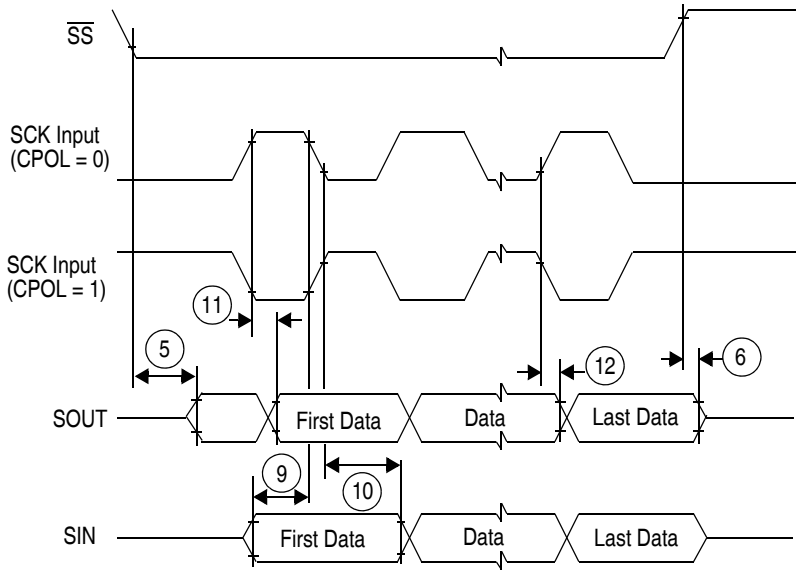
6 This parameter does not include the sample time t_{ADC0_S}, but only the time for determining the digital result and the time to load the result's register with the conversion result.

7 Total Unadjusted Error: The maximum error that occurs without adjusting Offset and Gain errors. This error is a combination of Offset, Gain and Integral Linearity errors.

3.18.2 DSPI characteristics

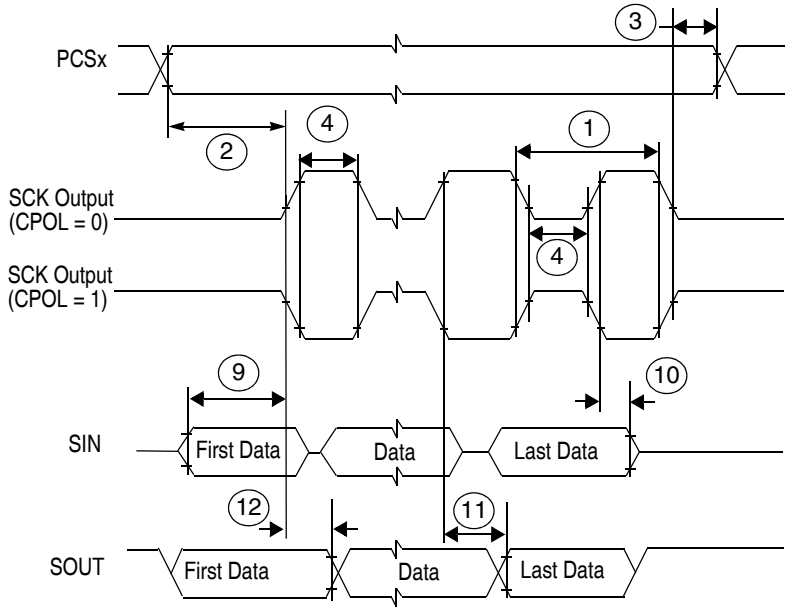
Table 44. DSPI characteristics[1]

No.	Symbol		C	Parameter		DSPI0/DSPI1/DSPI5/DSPI6			DSPI2/DSPI4			Unit
						Min	Typ	Max	Min	Typ	Max	
1	t_{SCK}	SR	D	SCK cycle time	Master mode (MTFE = 0)	125	—	—	333[2]	—	—	ns
			D		Slave mode (MTFE = 0)	125	—	—	333	—	—	
			D		Master mode (MTFE = 1)	83	—	—	145	—	—	
			D		Slave mode (MTFE = 1)	83	—	—	145	—	—	
—	f_{DSPI}	SR	D	DSPI digital controller frequency		—	—	f_{CPU}	—	—	f_{CPU}	MHz
2	t_{CSCext}[3]	SR	D	CS to SCK delay	Slave mode	32	—	—	32	—	—	ns
3	t_{ASCext}[4]	SR	D	After SCK delay	Slave mode	$1/f_{DSPI} + 5$	—	—	$1/f_{DSPI} + 5$	—	—	ns
4	t_{SDC}	CC	D	SCK duty cycle	Master mode	—	$t_{SCK}/2$	—	—	$t_{SCK}/2$	—	ns
		SR	D		Slave mode	$t_{SCK}/2$	—	—	$t_{SCK}/2$	—	—	
5	t_A	SR	D	Slave access time	Slave mode	—	—	$1/f_{DSPI} + 70$	—	—	$1/f_{DSPI} + 130$	ns
6	t_{DI}	SR	D	Slave SOUT disable time	Slave mode	7	—	—	7	—	—	ns
7	t_{PCSC}	CC	D	PCS*x* to $\overline{PCSS}$ time	—	13[5]	—	—	13[5]	—	—	
8	t_{PASC}	CC	D	$\overline{PCSS}$ to PCS*x* time	—	13[5]	—	—	13[5]	—	—	
9	t_{SUI}	SR	D	Data setup time for inputs	Master mode	43	—	—	145	—	—	ns
					Slave mode	5	—	—	5	—	—	
10	t_{HI}	SR	D	Data hold time for inputs	Master mode	0	—	—	0	—	—	ns
					Slave mode	2[6]	—	—	2[6]	—	—	
11	t_{SUO}[7]	CC	D	Data valid after SCK edge	Master mode	—	—	32	—	—	50	ns
					Slave mode	—	—	52	—	—	160	
12	t_{HO}[7]	CC	D	Data hold time for outputs	Master mode	0	—	—	0	—	—	ns
					Slave mode	8	—	—	13	—	—	



Note: Numbers shown reference Table 44.

Figure 26. DSPI classic SPI timing — slave, CPHA = 1



Note: Numbers shown reference Table 44.

Figure 27. DSPI modified transfer format timing — master, CPHA = 0

Table 45. JTAG characteristics (continued)

No.	Symbol		C	Parameter	Value			Unit
					Min	Typ	Max	
4	t_{TMSS}	CC	D	TMS setup time	15	—	—	ns
5	t_{TMSH}	CC	D	TMS hold time	5	—	—	ns
6	t_{TDOV}	CC	D	TCK low to TDO valid	—	—	33	ns
7	t_{TDOI}	CC	D	TCK low to TDO invalid	6	—	—	ns

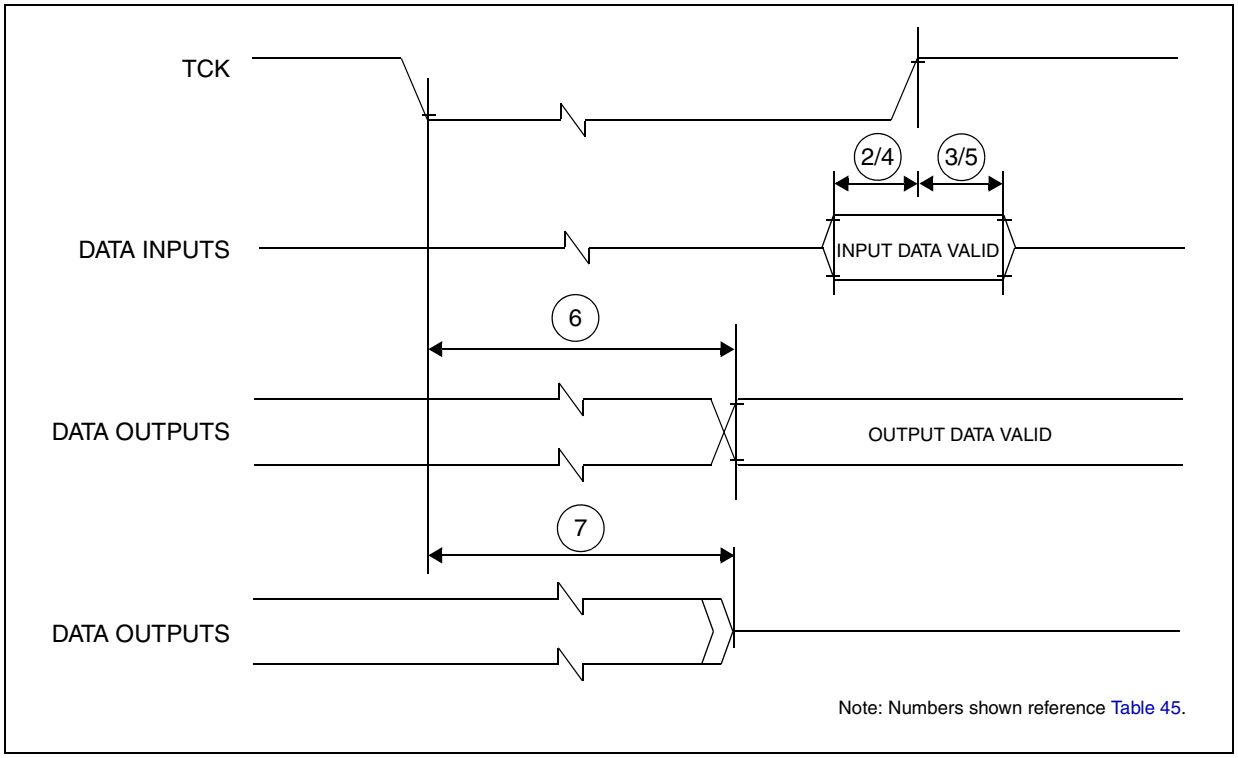
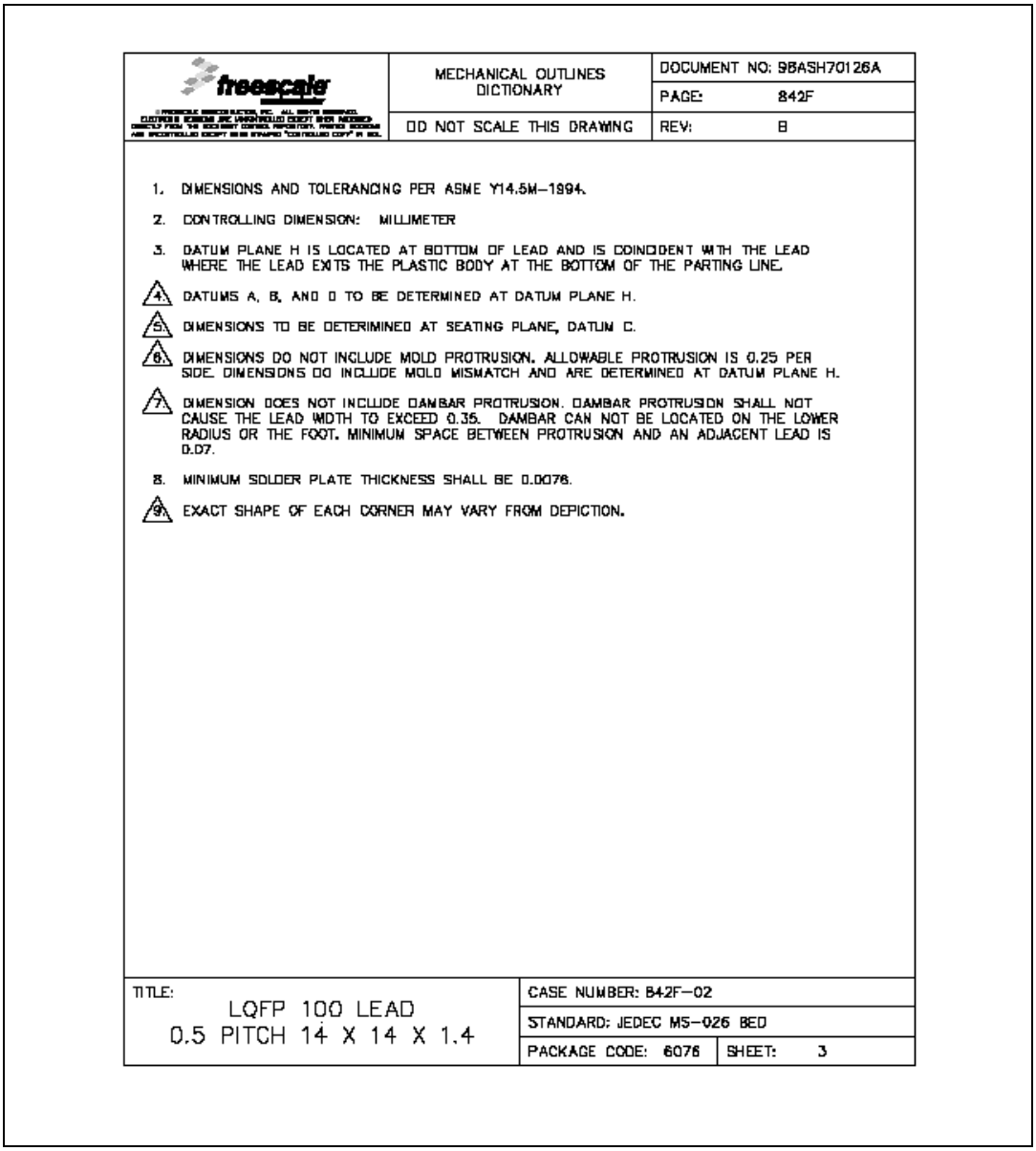


Figure 32. Timing diagram — JTAG boundary scan



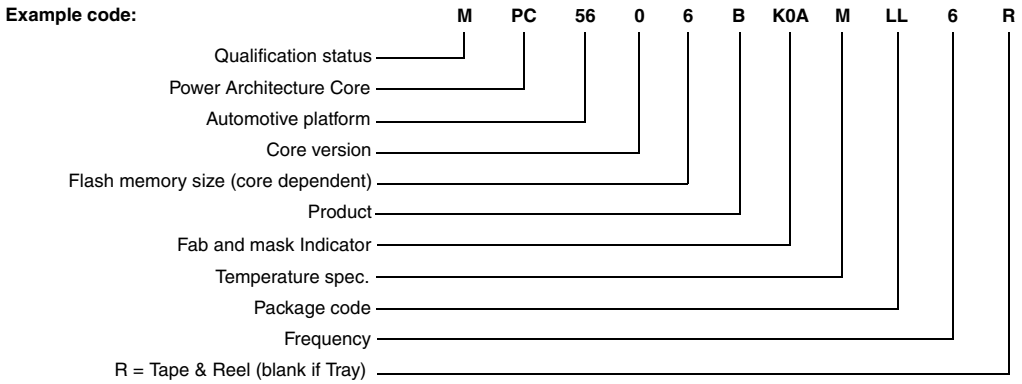
freescale	MECHANICAL OUTLINES DICTIONARY	DOCUMENT NO: 98ASH70126A
		PAGE: 842F
	DO NOT SCALE THIS DRAWING	REV: B

1. DIMENSIONS AND TOLERANCING PER ASME Y14.5M–1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DATUM PLANE H IS LOCATED AT BOTTOM OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE BOTTOM OF THE PARTING LINE.
4. DATUMS A, B, AND D TO BE DETERMINED AT DATUM PLANE H.
5. DIMENSIONS TO BE DETERIMINED AT SEATING PLANE, DATUM C.
6. DIMENSIONS DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 PER SIDE. DIMENSIONS DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE H.
7. DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED 0.35. DAMBAR CAN NOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSION AND AN ADJACENT LEAD IS 0.07.
8. MINIMUM SOLDER PLATE THICKNESS SHALL BE 0.0076.
9. EXACT SHAPE OF EACH CORNER MAY VARY FROM DEPICTION.

TITLE: LQFP 100 LEAD 0.5 PITCH 14 X 14 X 1.4	CASE NUMBER: 842F–02	
	STANDARD: JEDEC MS–026 BED	
	PACKAGE CODE: 6076	SHEET: 3

Figure 40. 100 LQFP package mechanical drawing (Part 3 of 3)

5 Ordering information



Qualification status
M = General market qualified
S = Automotive qualified
P = Engineering samples

Automotive Platform
56 = Power Architecture in 90nm

Core version
0 = e200z0

Flash memory size (for z0 core)
5 = 768 KB
6 = 1024 KB

Product
B = Body

Fab and mask Indicator
K = TSMC Fab
0 = Version of the maskset
A = Mask set indicator (Blank = 1st production maskset, A = 2nd, B = 3rd, etc)

Temperature spec.
C = –40 to 85 °C
V = –40 to 105 °C
M = –40 to 125 °C

Package code
LL = 100 LQFP
LQ = 144 LQFP
LU = 176 LQFP

Frequency
4 = Up to 48 MHz
6 = Up to 64 MHz

Note: Not all options are available on all devices.

Figure 41. Commercial product code structure

Table 46. Revision history (continued)

Revision	Date	Description of changes
2 (cont.)	15 May 2013	In Table 24 (Electrical characteristics in different application modes), — Changed I_{DDMAX} Typ to 81 mA and I_{DDMAX} Typ to 130 mA. — Changed I_{DDRUN} Typ for fCPU = 32 MHz to 40 mA. — Changed I_{DDRUN} Typ for fCPU = 48 MHz to 54 mA. Added I_{DDRUN} Max of 96 mA. — Changed I_{DDRUN} Typ for fCPU = 64 MHz to 67 mA. Added I_{DDRUN} Max of 120 mA. — Changed I_{DDHALT} at T_A = 25 °C Typ to 10 mA and I_{DDHALT} Max to 15 mA. — Changed I_{DDHALT} at T_A = 125 °C Typ to 15 mA and I_{DDHALT} Max to 28 mA. — Changed I_{DDSTOP} T_A temperature from –40 °C to 25 °C. — Changed I_{DDSTOP} at T_A = 25 °C Typ to 130 µA and I_{DDSTOP} Max to 500 µA. — Changed I_{DDSTOP} at T_A = 55 °C Typ to 180 µA. — Changed I_{DDSTOP} at T_A = 85 °C Typ to 1 mA and I_{DDSTOP} Max to 5 mA. — Changed I_{DDSTOP} at T_A = 105 °C Typ to 3 mA and I_{DDSTOP} Max to 9 mA. — Changed I_{DDSTOP} at T_A = 125 °C Typ to 5 mA and I_{DDSTOP} Max to 14 mA. — Changed $I_{DDSTDBY2}$ at T_A = 25 °C Typ to 17 µA and Max to 80 µA. — Changed $I_{DDSTDBY2}$ at T_A = 55 °C Typ to 30 µA. — Changed $I_{DDSTDBY2}$ at T_A = 85 °C Typ to 100 µA. — Changed $I_{DDSTDBY2}$ at T_A = 105 °C Typ to 280 µA and Max to 950 µA. — Changed $I_{DDSTDBY2}$ at T_A = 125 °C Typ to 460 µA and Max to 1700 µA. — Changed the parameter classification for $I_{DDSTANDBY2}$ (T_A = 125 °C) — Changed $I_{DDSTDBY1}$ at T_A = 25 °C Typ to 12 µA and Max to 50 µA. — Changed $I_{DDSTDBY1}$ at T_A = 55 °C Typ to 24 µA. — Changed $I_{DDSTDBY1}$ at T_A = 85 °C Typ to 48 µA. — Changed $I_{DDSTDBY1}$ at T_A = 105 °C Typ to 150 µA and Max to 500 µA. — Changed $I_{DDSTDBY1}$ at T_A = 125 °C Typ to 260 µA. — Changed the third sentence of Footnote 3 to begin with “The given value is thought to be a **worst case value** (64 MHz at 125 °C) with all peripherals running.” — Removed footnotes 8 and 9 regarding I_{DDHALT} and I_{DDSTOP}. — Corrected “C” characteristics to reflect testing status. In Section 3.10, Flash memory electrical characteristics, removed the "FLASH_BIU settings vs. frequency of operation" table. In Table 28 (Flash power supply DC electrical characteristics), corrected Footnote 2 to specify 125 °C. In Section 3.14, FMPLL electrical characteristics, changed the text “the main oscillator driver” to “the FXOSC or FIRC sources.” In Table 40 (ADC input leakage current), added specifications for 85 °C. In Table 44 (DSPI characteristics), added t_{SCK} specifications for MTFE=1. In Table 44 (DSPI characteristics), updated specifications 7 and 8 to 13 ns, all DSPIs. in ADC section, corrected Equation 11. In Figure 41 (Commercial product code structure), added “**Note:** Not all options are available on all devices.” Removed Section 6, Abbreviations.
3	11 Sep 2013	Updated the temperature in table note 2 in Table 1 (MPC5606BK family comparison) from 105 ^{o}C to 125 ^{o}C.
4	25 Nov2015	Updated the Max value current for $I_{ADC0run}$ from 40 mA to 5 mA in Table 41 (ADC_0 conversion characteristics (10-bit ADC_0)).
5	7 Nov 2017	In Table 9 (Recommended operating conditions (3.3 V)) added Min value for TV_{DD}. In Table 10 (Recommended operating conditions (5.0 V)) added Min value for TV_{DD}. In Table 44 (DSPI characteristics) changed the for DSPI 2 and 4, in MTFE=1 mode from 125 to 145.